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V41M103C

Vishay General Semiconductor

# Dual High Voltage TMBS<sup>®</sup> (Trench MOS Barrier Schottky) Rectifier

Ultra Low  $V_F = 0.40$  V at  $I_F = 5$  A

## **FEATURES**

- Trench MOS Schottky technology
- Low forward voltage drop, low power losses
- · High efficiency operation
- Solder bath temperature 275 °C maximum, 10 s, FREE per JESD 22-B106
- · Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

## TYPICAL APPLICATIONS

For use in high frequency converters, switching power supplies, freewheeling diodes, OR-ing diode, DC/DC converters, and reverse battery protection.

### **MECHANICAL DATA**

Case: TO-220AB

Molding compound meets UL 94 V-0 flammability rating Base P/N-M3 - halogen-free, RoHS-compliant, and commercial grade

Terminals: matte tin plated leads, solderable per J-STD-002 and JESD 22-B102

M3 suffix meets JESD 201 class 1A whisker test

Polarity: as marked

Mounting Torque: 10 in-lbs maximum

<b>MAXIMUM RATINGS</b> (T <sub>A</sub> = 25 °C unless otherwise noted)				
PARAMETER		SYMBOL	V41M103C	UNIT
Maximum repetitive peak reverse voltage		V <sub>RRM</sub>	100	V
Maximum average forward rectified current (fig. 1)	per device	I	40	A
	per diode	I <sub>F(AV)</sub>	20	
Peak forward surge current 8.3 ms single half sine-wave on rated load per diode	I <sub>FSM</sub>	250	А	
Operating junction temperature range		T <sub>J</sub> <sup>(1)</sup>	-40 to +175	°C
Storage temperature range		T <sub>STG</sub>	-55 to +175	

Note

<sup>(1)</sup> The heat generated must be less than the thermal conductivity from junction to ambient:  $dP_D/dT_J < 1/R_{0,JA}$ 



PRIMARY CHARACTERISTICS					
I <sub>F(AV)</sub>	2 x 20 A				
V <sub>RRM</sub>	100 V				
I <sub>FSM</sub>	250 A				
V <sub>F</sub> at I <sub>F</sub> = 20 A (125 °C)	0.59 V				
T <sub>J</sub> max.	175 °C				
Package	TO-220AB				
Circuit configuration	Common cathode				





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<b>ELECTRICAL CHARACTERISTICS</b> ( $T_J$ = 25 °C unless otherwise noted)							
PARAMETER	TEST CONDITIONS		SYMBOL	TYP.	MAX.	UNIT	
Instantaneous forward voltage per diode	I <sub>F</sub> = 5 A	T <sub>J</sub> = 25 °C	V <sub>F</sub> <sup>(1)</sup>	0.49	-	V	
	I <sub>F</sub> = 10 A			0.56	-		
	I <sub>F</sub> = 20 A			0.67	0.73		
	I <sub>F</sub> = 5 A	T <sub>J</sub> = 125 °C		0.40	-		
	I <sub>F</sub> = 10 A			0.49	-		
	I <sub>F</sub> = 20 A			0.59	0.65		
Reverse current at rated V <sub>R</sub> per diode	V <sub>B</sub> = 70 V	T <sub>J</sub> = 25 °C	I <sub>R</sub> (2)	0.005	-	mA	
	v <sub>R</sub> = 70 v	T <sub>J</sub> = 125 °C		3.2	-		
	V <sub>R</sub> = 100 V	T <sub>J</sub> = 25 °C		-	0.4		
		T <sub>J</sub> = 125 °C		8.0	45		
Typical junction capacitance	4 V, 1MHz	-	CJ	2500	-	pF	

#### Notes

 $^{(2)}\,$  Pulse test: 300  $\mu s$  pulse width, 1 % duty cycle

<sup>(3)</sup> Pulse test: Pulse width  $\leq$  5 ms

<b>THERMAL CHARACTERISTICS</b> ( $T_A = 25 \text{ °C}$ unless otherwise noted)				
PARAMETER	SYMBOL	V41M103C	UNIT	
Typical thermal resistance per device	R <sub>0JC</sub> <sup>(1)</sup>	1.0	°C/W	

#### Note

<sup>(4)</sup> Thermal resistance junction-to-case to follow JEDEC<sup>®</sup> 51-14 transient dual interface test method (TDIM)

OERDERING INFORMATION (Example)						
PREFERRED P/N	UNIT WEIGHT (g)	PACKAGE CODE	BASE QUANTITY	DELIVERY MODE		
V41M103C-M3/P	1.88	Р	50/tube	Tube		



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## **RATINGS AND CHARACTERISTICS CURVES** ( $T_A = 25$ °C unless otherwise noted)

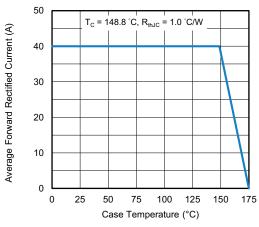


Fig. 1 - Forward Current Derating Curve

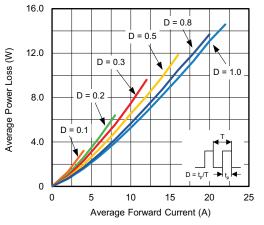


Fig. 2 - Forward Power Loss Characteristics Per Diode

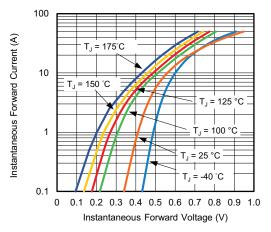


Fig. 3 - Typical Instantaneous Forward Characteristics Per Diode

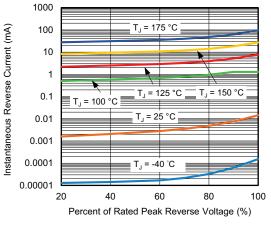
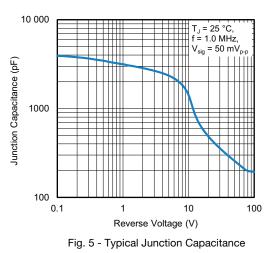
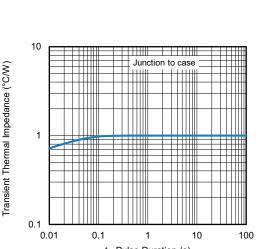


Fig. 4 - Typical Reverse Characteristics Per Diode





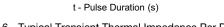


Fig. 6 - Typical Transient Thermal Impedance Per Device

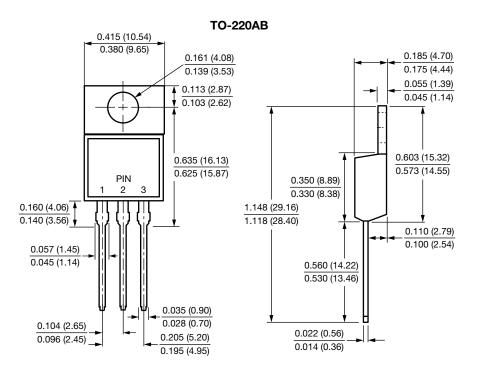
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## **PACKAGE OUTLINE DIMENSIONS** in inches (millimeters)





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